

Session Program

13-15 Nov 2013

23rd RD50 Workshop (CERN)

Device Simulations and some key experimental data

CERN

503-1-001 (Council Chamber) on 13th Nov & 222-R-001 (Filtration Plant) on 14th & 15th Nov.

Thursday 14 November

12:25

Device Simulations and some key experimental data

Session |

Location: CERN, 503-1-001 (Council Chamber) on 13th Nov & 222-R-001 (Filtration Plant) on 14th & 15th Nov. |

Convener: Vladimir Eremin

12:25-13:35 **Lunch Break**

13:35-13:55 **TCAD for Radiation, a review**

Speaker

Dr Fco. Rogelio Palomo Pinto

13:55-14:15 **A Single Event Effects tool for VLSI designers**

Speaker

Dr Fco. Rogelio Palomo Pinto

14:15-14:35

Experimental study of the Si-SO₂ interface region in p+n-silicon strip sensors before and after X-ray irradiation

Speaker

Thomas Poehlsen

14:35-14:55

Simulations of Hadron Irradiated n+p- Si Strip Sensors Incorporating Bulk and Surface Damage

Speaker

Ranjeet Ranjeet

14:55-15:15

Non-uniform 3-level defect model and status of edge-TCT simulations

Speaker

Timo Hannu Tapani Peltola

15:15-15:45

Coffee Break

15:45-16:05

Contribution from $E_g(T)$ dependence into parameterization of the bulk generation current of irradiated Si detectors

Speaker

Dr Vladimir Eremin

16:05-16:25

Update on the temperature dependence of the bulk current in Si (remote)

Speaker

Alexandre Chilingarov

16:25-16:45

Trapping related negative feedback as the reason for collected charge restriction in heavily irradiated Si detectors operating with avalanche multiplication

Speaker

Dr Elena Verbitskaya

16:45–17:05

Comparison of Radiation Hardness Properties of p+n- & n+p- Si Strip Sensors Using Simulation Approach**Speaker**

Ranjeet Ranjeet

17:05–17:25

TCAD simulations and beam tests: measuring the electric field in irradiates sensors**Speaker**

Marco Bomben

17:25–17:45

T-CAD simulation of Lorentz angle**Speaker**

Andreas Matthias Nurnberg

17:45–18:45

Discussion on Simulations**Speaker**

Vladimir Eremin

19:10